Transistors

# 4V Drive Pch MOSFET **RSR015P03**

### Structure

Silicon P-channel MOSFET

### Features

- 1) Low On-resistance
- 2) Space saving-small surface mount package (TSMT3)
- 3) 4V drive

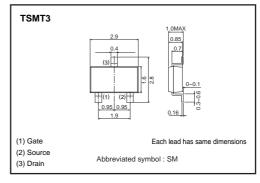
## Applications

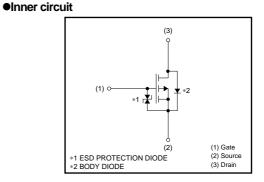
Switching

#### Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RSR015P03	0		

## •Dimensions (Unit : mm)





#### Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Droin ourrant	Continuous	ID	±1.5	А	
Drain current	Pulsed	I <sub>DP</sub> *1	±6	А	
Source current	Continuous	ls	-0.5	А	
(Body diode)	Pulsed	Isp *1	-6	А	
Total power dissipation		P <sub>D</sub> *2	1	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1%\*2 Mounted on a ceramic board

#### Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	125	°C/W	

\* Mounted on a ceramic board



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## •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μΑ	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	-30	-	-	V	I <sub>D</sub> = –1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	-1	μΑ	$V_{DS}$ = -30V, $V_{GS}$ =0V
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$
Static drain-source on-state resistance		_	170	235	mΩ	I <sub>D</sub> = -1.5A, V <sub>GS</sub> = -10V
	$R_{DS(on)^*}$	-	270	375	mΩ	I <sub>D</sub> = -0.8A, V <sub>GS</sub> = -4.5V
		-	320	440	mΩ	I <sub>D</sub> = -0.8A, V <sub>GS</sub> = -4V
Forward transfer admittance	Y <sub>fs</sub> *	0.9	-	_	S	$V_{DS} = -10V, I_{D} = -0.8A$
Input capacitance	Ciss	_	190	_	pF	V <sub>DS</sub> =-10V
Output capacitance	Coss	-	45	-	рF	Vgs=0V
Reverse transfer capacitance	Crss	-	30	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	6	-	ns	Vdd≒-15V
Rise time	tr *	-	8	_	ns	$I_{D} = -0.8A$
Turn-off delay time	td (off) *	-	22	-	ns	Vgs= –10V R∟=19Ω
Fall time	t <sub>f</sub> *	-	6	-	ns	Rg=10Ω
Total gate charge	Qg *	-	2.6	_	nC	V <sub>DD</sub> ≒-15V V <sub>GS</sub> =-5V
Gate-source charge	Q <sub>gs</sub> *	-	1.0	-	nC	I <sub>D</sub> = –1.5A
Gate-drain charge	Q <sub>gd</sub> *	-	0.7	-	nC	R∟=10Ω R <sub>G</sub> =10Ω

## •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd		-	-1.2	V	Is= -0.5A, V <sub>GS</sub> =0V

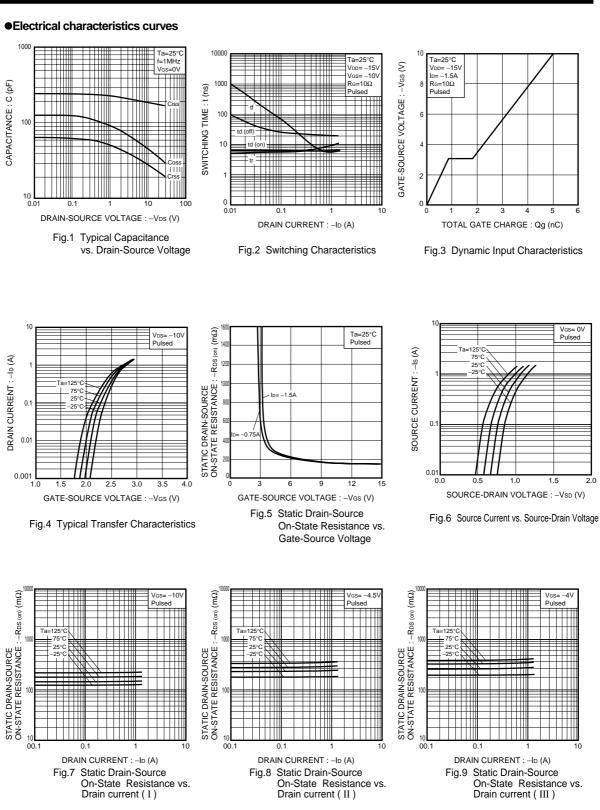
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Vgs= 0V Pulsed

1.5

2.0

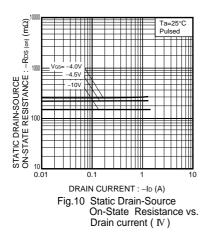
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